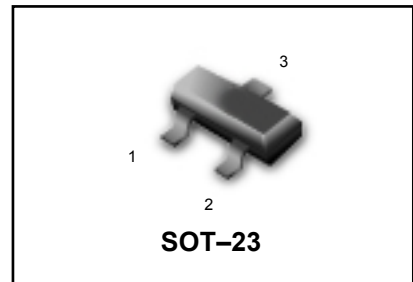


General Purpose Transistor

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**MMBT3904LT1
S-MMBT3904LT1**

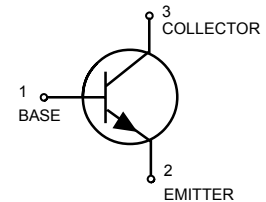


ORDERING INFORMATION

Device	Marking	Shipping
MMBT3904LT1 S-MMBT3904LT1	1AM (Made in China) 7AP (Made in Hong Kong)	3000/Tape & Reel
MMBT3904LT3 S-MMBT3904LT3	1AM (Made in China) 7AP (Made in Hong Kong)	10000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage(3) ($I_C = 1.0 \text{ mAdc}$)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc},$)	I_{BL}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	—	50	nAdc

1. FR–5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$
2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.
3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS (3)				
DC Current Gain(1) ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	40	—	—
($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		70	—	
($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		100	300	
($I_C = 50 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		60	—	
($I_C = 100 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		30	—	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)(3)	$V_{CE(sat)}$	—	0.2	Vdc
($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)		—	0.3	
Base–Emitter Saturation Voltage(3) ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)	$V_{BE(sat)}$	0.65	0.85	Vdc
($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)		—	0.95	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	—	8.0	pF
Input Impedance ($V_{CE} = 10 \text{ Vdc}$, $I_C = 1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	1.0	10	$k\Omega$
Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}$, $I_C = 1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = 10 \text{ Vdc}$, $I_C = 1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	100	400	—
Output Admittance ($V_{CE} = 10 \text{ Vdc}$, $I_C = 1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	1.0	40	μmhos
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}$, $I_C = 100 \mu\text{Adc}$, $R_s = 1.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$)	NF	—	5.0	dB

SWITCHING CHARACTERISTICS

Delay Time ($V_{CC} = 3.0 \text{ Vdc}$, $V_{BE} = -0.5 \text{ Vdc}$)	t_d	—	35	ns
Rise Time ($I_C = 10 \text{ mAdc}$, $I_{B1} = 1.0 \text{ mAdc}$)	t_r	—	35	ns
Storage Time ($V_{CC} = 3.0 \text{ Vdc}$)	t_s	—	200	ns
Fall Time ($I_C = 10 \text{ mAdc}$, $I_{B1} = I_{B2} = 1.0 \text{ mAdc}$)	t_f	—	50	ns

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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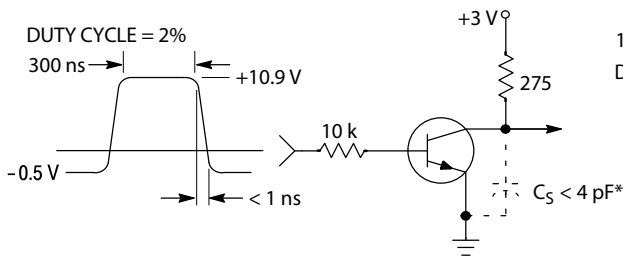


Figure 1. Delay and Rise Time Equivalent Test Circuit

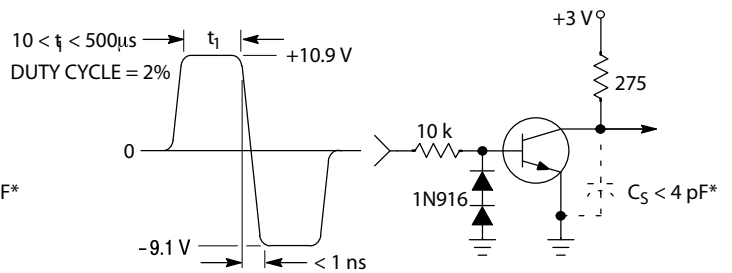


Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - - $T_J = 125^\circ\text{C}$

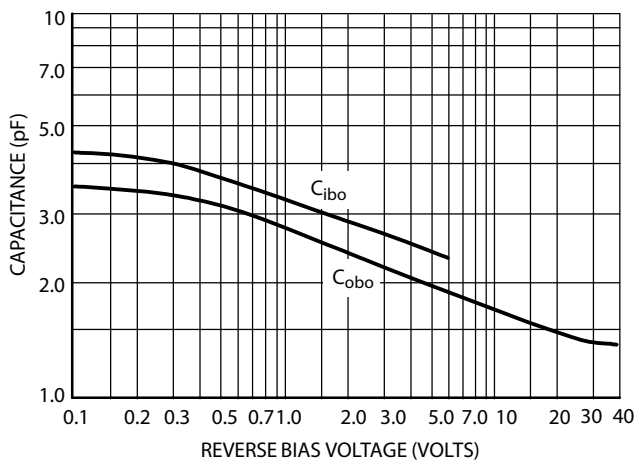


Figure 3. Capacitance

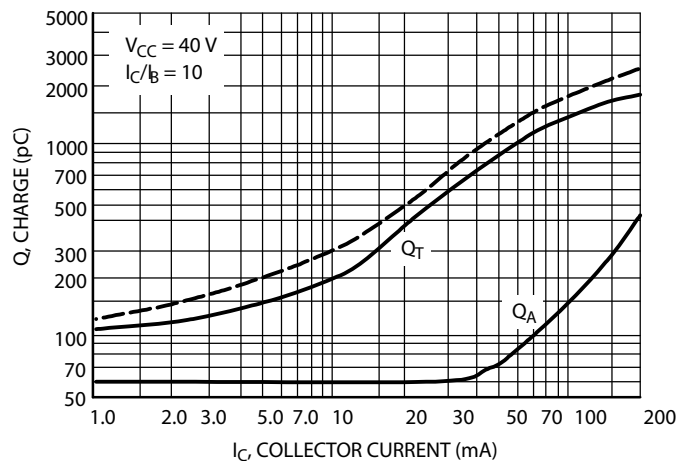


Figure 4. Charge Data

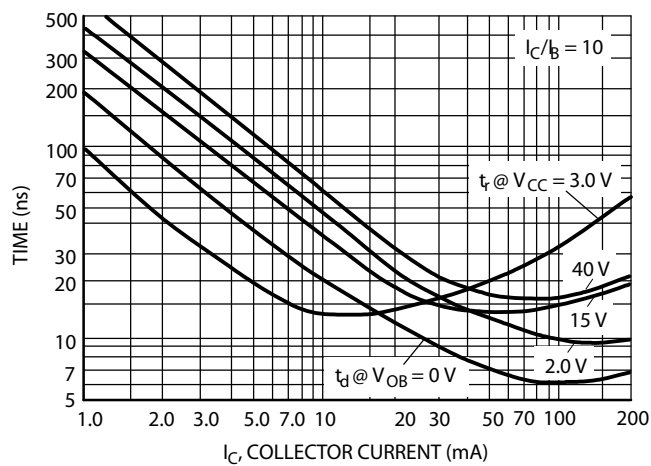


Figure 5. Turn-On Time

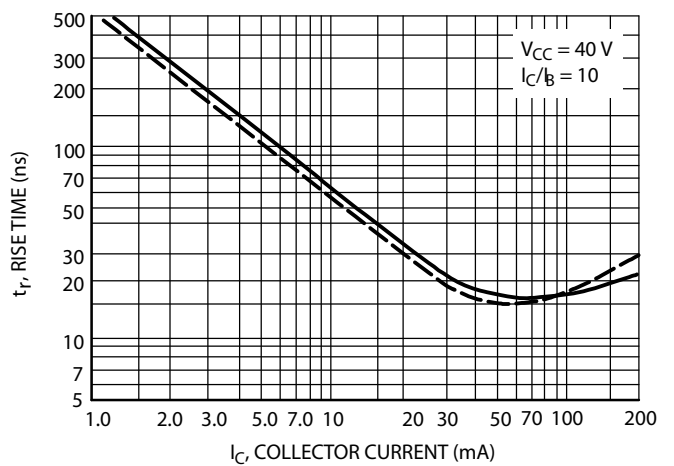


Figure 6. Rise Time

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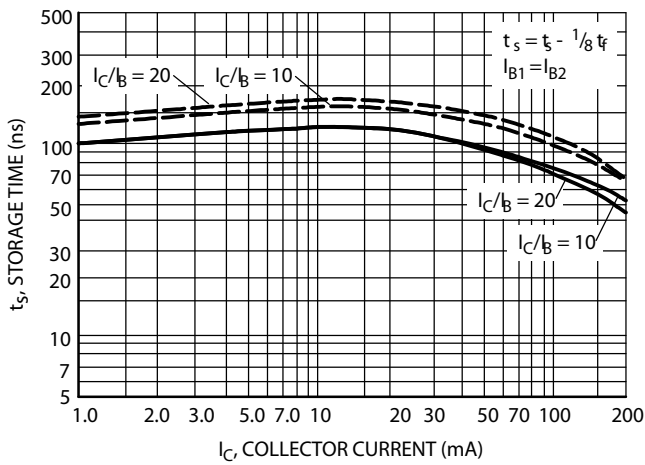


Figure 7. Storage Time

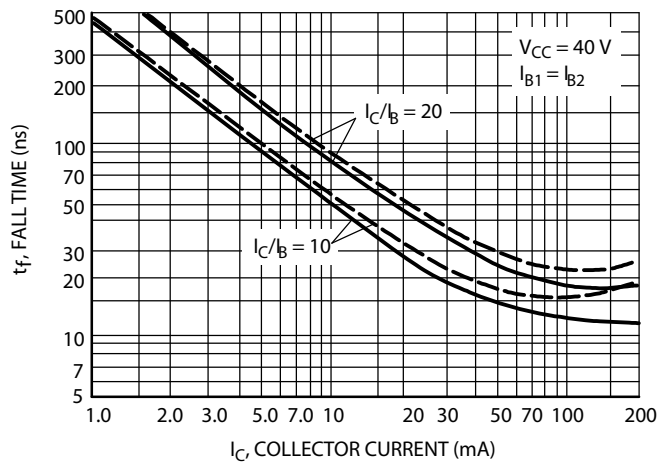


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

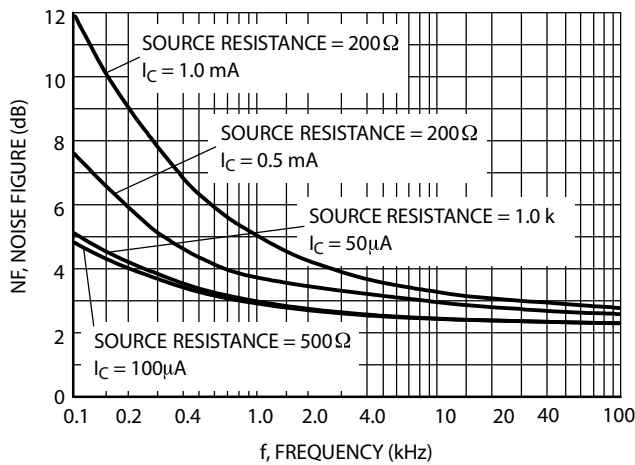


Figure 9.

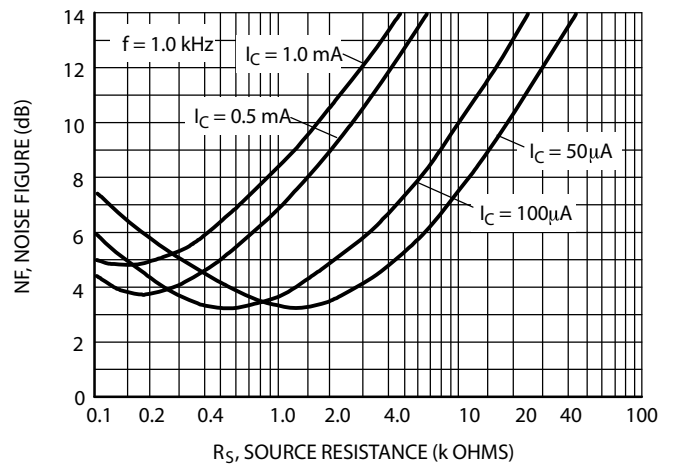


Figure 10.

h PARAMETERS

($V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

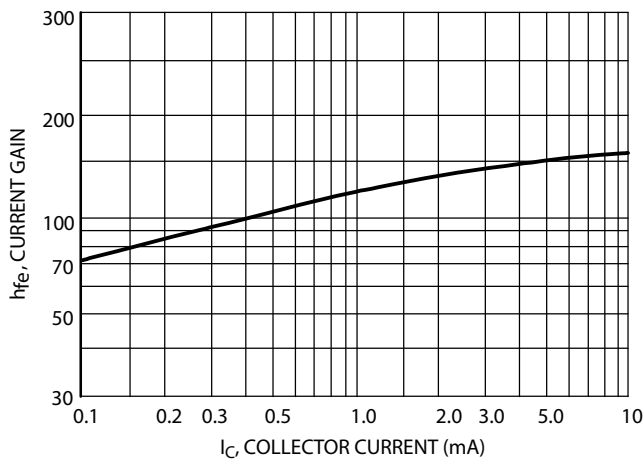


Figure 11. Current Gain

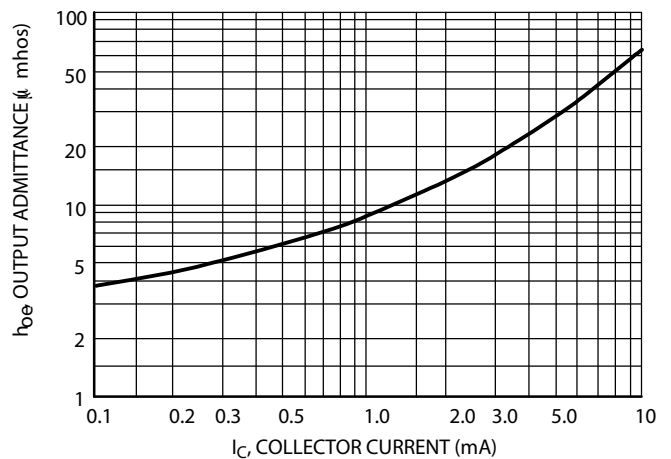


Figure 12. Output Admittance

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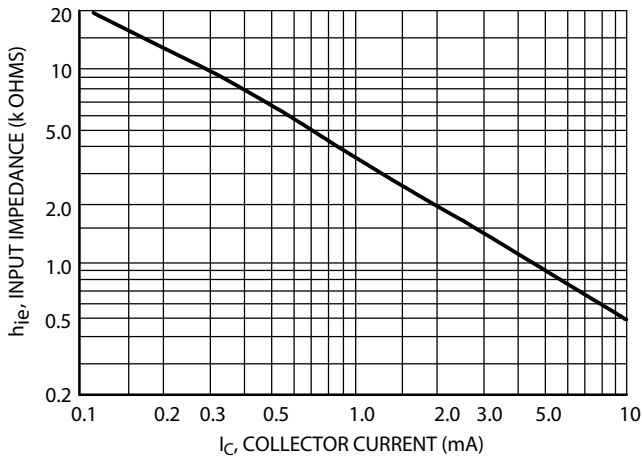


Figure 13. Input Impedance

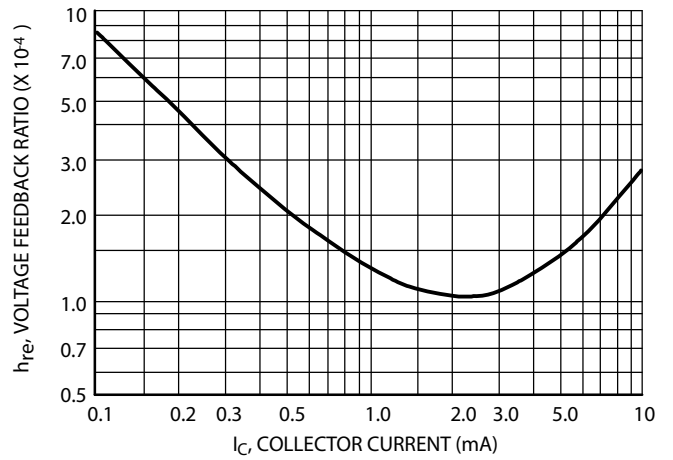


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

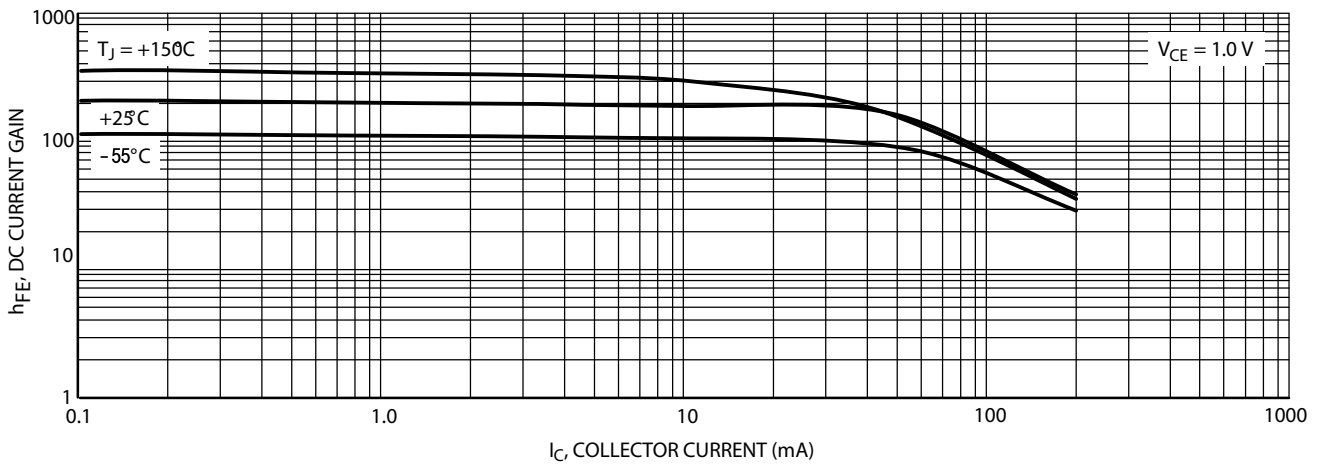


Figure 15. DC Current Gain

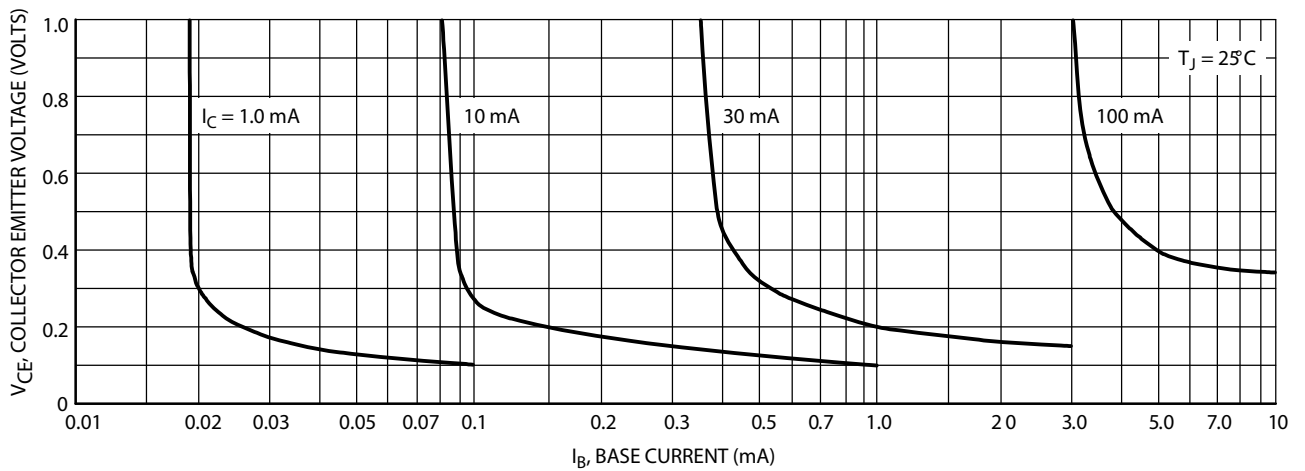


Figure 16. Collector Saturation Region

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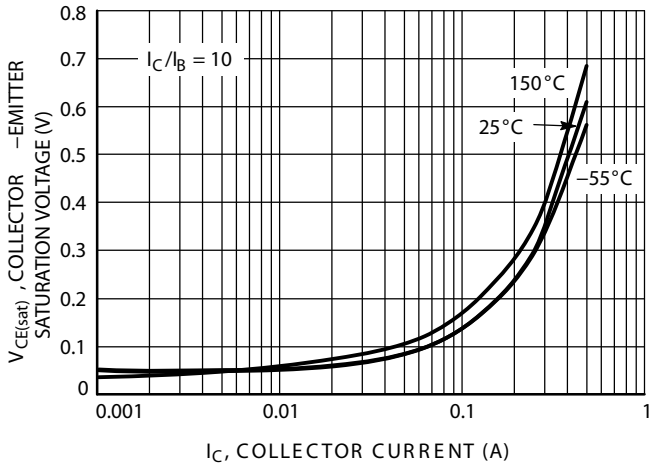


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

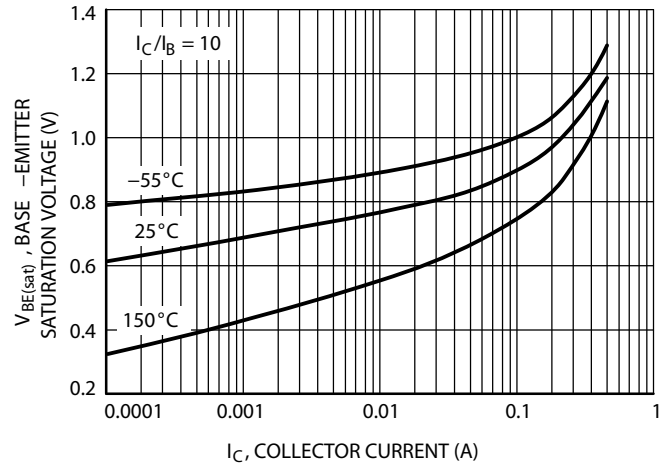


Figure 18. Base Emitter Saturation Voltage vs. Collector Current

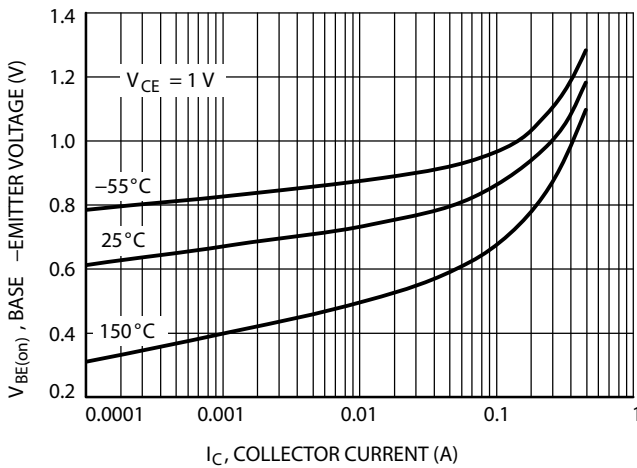


Figure 19. Base Emitter Voltage vs. Collector Current

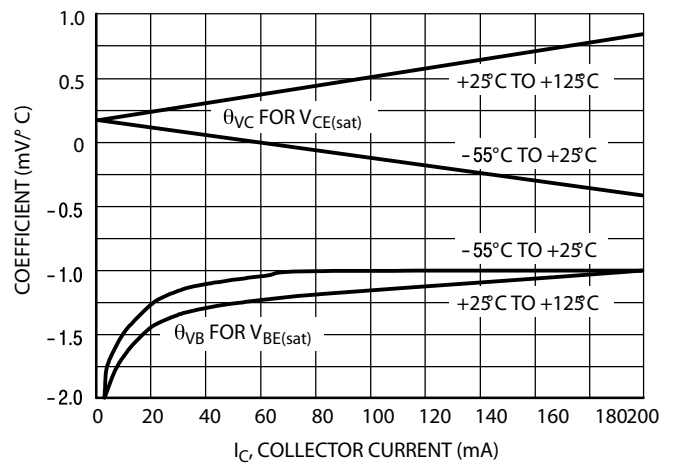


Figure 20. Temperature Coefficients

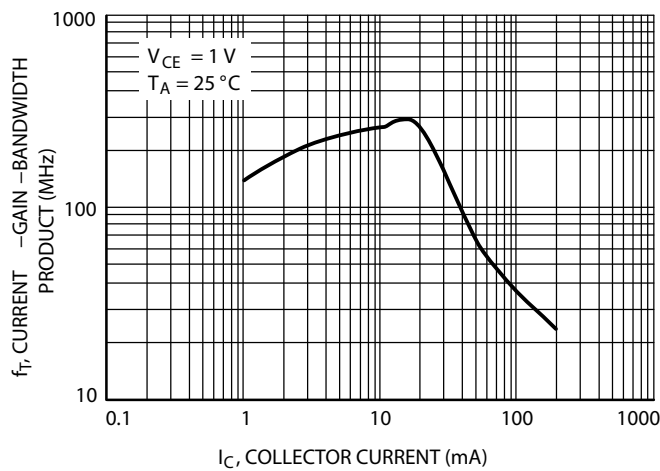


Figure 21. Current Gain Bandwidth vs. Collector Current

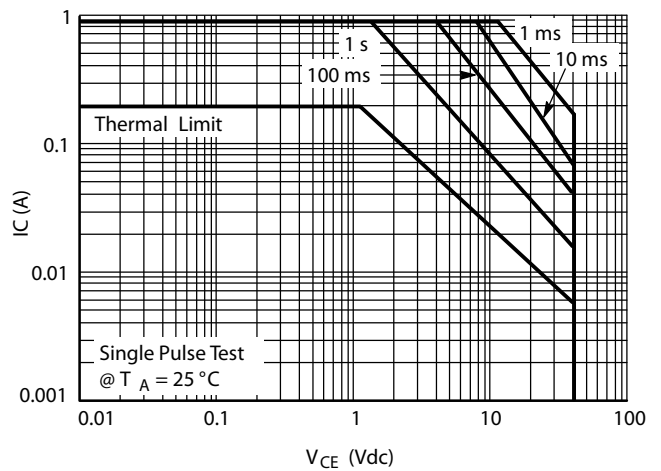
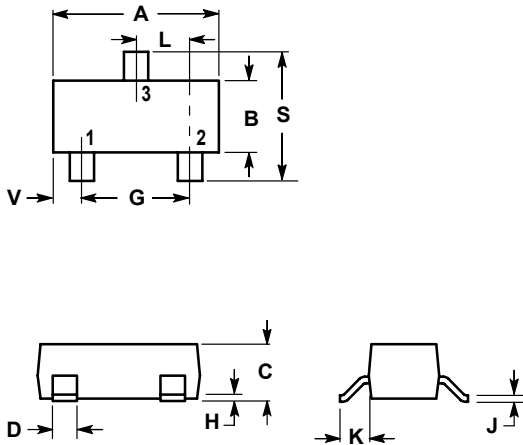


Figure 22. Safe Operating Area

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- P N 1. BASE
 2. EMITTER
 3. COLLECTOR

